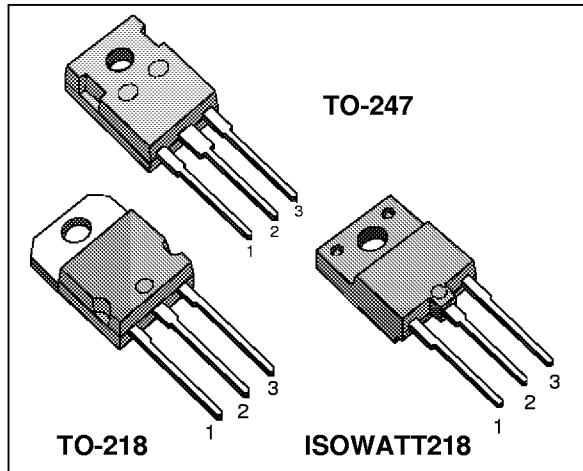


## N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STH75N06	60 V	< 0.014 Ω	75 A
STH75N06FI	60 V	< 0.014 Ω	48 A
STH75N06	60 V	< 0.014 Ω	75 A

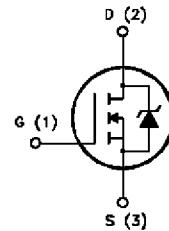
- TYPICAL R<sub>DS(on)</sub> = 0.011 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- VERY HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE
- APPLICATION ORIENTED CHARACTERIZATION



### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, Etc.)

### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW/STH75N06	STH75N06FI	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	60		V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	60		V
V <sub>GS</sub>	Gate-source Voltage	± 20		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	75	48	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	53	30	A
I <sub>DM(•)</sub>	Drain Current (pulsed)	300	300	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	200	70	W
	Derating Factor	1.33	0.56	W/°C
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	—	4000	V
T <sub>stg</sub>	Storage Temperature	-65 to 175	-65 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	175	150	°C

(•) Pulse width limited by safe operating area

## STH75N06/FI STW75N06

### THERMAL DATA

			TO-218/TO-247	ISOWATT218	
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	0.75	1.79	°C/W
R <sub>thj-amb</sub> R <sub>thc-sink</sub>	Thermal Resistance Junction-ambient Thermal Resistance Case-sink	Max Typ	30 0.1		°C/W °C/W
T <sub>I</sub>	Maximum Lead Temperature For Soldering Purpose		300		°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)	70	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 25 V)	900	mJ
E <sub>AR</sub>	Repetitive Avalanche Energy (pulse width limited by T <sub>j</sub> max, δ < 1%)	200	mJ
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (T <sub>c</sub> = 100 °C, pulse width limited by T <sub>j</sub> max, δ < 1%)	45	A

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating × 0.8 T <sub>c</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			± 100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>G(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2	2.9	4	V
R <sub>D(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 40 A		0.011	0.014	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>D(on)max</sub> V <sub>GS</sub> = 10 V	75			A

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>D(on)max</sub> I <sub>D</sub> = 40 A	25	45		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		4000 1800 500	5200 2300 650	pF pF pF

## ELECTRICAL CHARACTERISTICS (continued)

### SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Time Rise Time	$V_{DD} = 25 \text{ V}$ $I_D = 40 \text{ A}$ $R_G = 50 \Omega$ $V_{GS} = 10 \text{ V}$ (see test circuit, figure 3)		190 900	270 1300	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 40 \text{ V}$ $I_D = 75 \text{ A}$ $R_G = 50 \Omega$ $V_{GS} = 10 \text{ V}$ (see test circuit, figure 5)		150		$\text{A}/\mu\text{s}$
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 25 \text{ V}$ $I_D = 40 \text{ A}$ $V_{GS} = 10 \text{ V}$		130 27 48	180	nC nC nC

### SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ $t_f$ $t_c$	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 40 \text{ V}$ $I_D = 75 \text{ A}$ $R_G = 50 \Omega$ $V_{GS} = 10 \text{ V}$ (see test circuit, figure 5)		400 300 650	550 420 900	ns ns ns

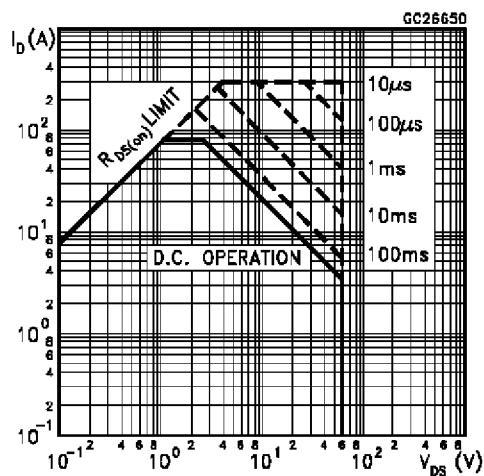
### SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				75 300	A A
$V_{SD} (\ast)$	Forward On Voltage	$I_{SD} = 75 \text{ A}$ $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 75 \text{ A}$ $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 35 \text{ V}$ $T_j = 150 \text{ }^\circ\text{C}$		130		ns
$Q_{rr}$	Reverse Recovery Charge	(see test circuit, figure 5)		0.45		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			7		A

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

( $\bullet$ ) Pulse width limited by safe operating area

### Safe Operating Areas For TO-218 and TO-247



### Safe Operating Areas For ISOWATT218

